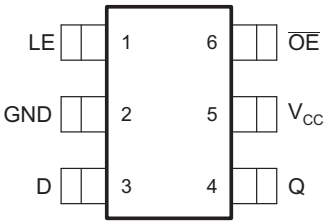
SN74LVC1G373
SINGLE D-TYPE LATCH
WITH 3-STATE OUPUT

SCES528C – DECEMBER 2003 – REVISED MAY 2007

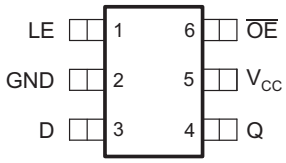
FEATURES

- **Available in the Texas Instruments NanoFree™ Package**
- **Supports 5-V V_{CC} Operation**
- **Inputs Accept Voltages to 5.5 V**
- **Max t_{pd} of 4 ns at 3.3 V**
- **Low Power Consumption, 10-μA Max I_{CC}**
- **±24-mA Output Drive at 3.3 V**
- **I_{off} Supports Partial-Power-Down Mode Operation**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Protection Exceeds JESD 22**
  - **2000-V Human-Body Model (A114-A)**
  - **200-V Machine Model (A115-A)**
  - **1000-V Charged-Device Model (C101)**

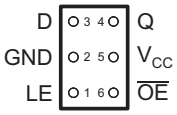
DBVP ACKAGE
(TOP VIEW)



DCKP ACKAGE
(TOP VIEW)



YZP PACKAGE
(BOTTOMVIEW)



Seemechanicaldrawingsfordimensions.

DESCRIPTION/ORDERING INFORMATION

This single D-type latch is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G373 is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

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NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

ORDERING INFORMATION

T_A	PACKAGE(1)(2)		ORDERING PART NUMBER	TOP-SIDE MARKING(3)
–40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Reel of 3000	SN74LVC1G373YZPR	_ _ _D3_
	SOT (SOT-23) – DBV	Reel of 3000	SN74LVC1G373DBVR	CA3_
		Reel of 250	SN74LVC1G373DBVT	
	SOT (SC-70) – DCK	Reel of 3000	SN74LVC1G373DCKR	D3_
		Reel of 250	SN74LVC1G373DCKT	

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.
(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
(3) DCK: The actual top-side marking has one additional character that designates the assembly/test site.
YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

DESCRIPTION/ORDERING INFORMATION (CONTINUED)

$\overline{OE}$ does not affect the internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

A buffered output-enable ($\overline{OE}$) input can be used to place the output in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the output neither loads nor drives the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

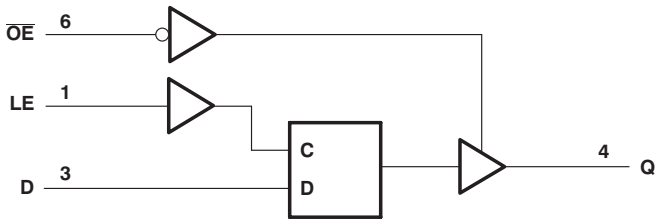
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

FUNCTION TABLE

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	L	L
L	H	H	H
L	L	X	Q_0
H	X	X	Z

LOGIC DIAGRAM (POSITIVE LOGIC)



Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	6.5	V
V_I	Input voltage range(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high-impedance or power-off state(2)(3)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high or low state(2)(3)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	$V_I < 0$		–50	mA
I_{OK}	Output clamp current	$V_O < 0$		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
θ_{JA}	Package thermal impedance(4)	DBV package		165	°C/W
		DCK package		259	
		YZP package		123	
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
(3) The value of V_{CC} is provided in the recommended operating conditions table.
(4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
		V_{CC} = 3 V to 3.6 V	2		
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}		
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
		V_{CC} = 3 V to 3.6 V		0.8	
		V_{CC} = 4.5 V to 5.5 V		0.3 × V_{CC}	
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4	mA
		V_{CC} = 2.3 V		–8	
		V_{CC} = 3 V		–16	
				–24	
		V_{CC} = 4.5 V		–32	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4	mA
		V_{CC} = 2.3 V		8	
		V_{CC} = 3 V		16	
				24	
		V_{CC} = 4.5 V		32	
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V_{CC} = 3.3 V ± 0.3 V		10	
		V_{CC} = 5 V ± 0.5 V		5	
T_A	Operating free-air temperature		–40	85	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	MIN	TYP(1)	MAX	UNIT
V_{OH}	I_{OH} = –100 μA	1.65 V to 5.5 V	V_{CC} – 0.1			V
	I_{OH} = –4 mA	1.65 V	1.2			
	I_{OH} = –8 mA	2.3 V	1.9			
	I_{OH} = –16 mA	3 V	2.4			
	I_{OH} = –24 mA		2.3			
	I_{OH} = –32 mA	4.5 V	3.8			
V_{OL}	I_{OL} = 100 μA	1.65 V to 5.5 V			0.1	V
	I_{OL} = 4 mA	1.65 V			0.45	
	I_{OL} = 8 mA	2.3 V			0.3	
	I_{OL} = 16 mA	3 V			0.4	
	I_{OL}= 24 mA				0.55	
	I_{OL}= 32 mA	4.5 V			0.55	
I_I	V_I = 5.5 V or GND	0 to 5.5 V			±1	μA
I_{OZ}	V_O = 0 to 5.5 V	3.6 V			±5	
I_{off}	V_I or V_O = 5.5 V	0			±10	
I_{CC}	V_I = 5.5 V or GND, I_O = 0	1.65 V to 5.5 V			10	
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 5.5 V			500	
C_i	V_I = V_{CC} or GND	3.3 V		3.5		pF
C_o	V_O = V_{CC} or GND	3.3 V		6		

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

Timing Requirements

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3		3		3		3		ns
t_{su}	Setup time, data before LE↓	2.4		2		1.5		1.5		ns
t_h	Hold time, data after LE↓	2.5		1.5		1.5		1.5		ns

Switching Characteristics

over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM INPUT	TO (OUTPUT)	V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	D	Q	2	15	1.5	5	1	4	1	3.5	ns
	LE		2	15	1.5	5	1	4	1	3.5	
t_{en}	$\overline{OE}$	Q	2	12.5	1.5	4.5	1	4	1	2.5	ns
t_{dis}	$\overline{OE}$	Q	2	14	1.5	7	1	7.9	1	5.3	ns

Switching Characteristics

over recommended operating free-air temperature range, C_L = 30 pF or 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM INPUT	TO (OUTPUT)	V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	D	Q	2	16	1.5	7.3	1	5.4	1	4	ns
	LE		2	16.3	1.5	7.4	1	5.5	1	4	
t_{en}	$\overline{OE}$	Q	2	13	1.5	6.3	1	5.1	1	3.7	ns
t_{dis}	$\overline{OE}$	Q	2	17.4	1	5.9	1	6.5	1	4.6	ns

Operating Characteristics

T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	V_{CC} = 5 V	UNIT
				TYP	TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	f = 10 MHz	19	19	19	20	pF
		Outputs disabled		3	3	3	4	